

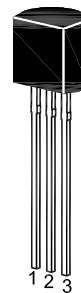
2N5400 / 2N5401

PNP Silicon Epitaxial Planar Transistors

for general purpose, high voltage amplifier applications.

As complementary types the NPN transistors 2N5550 and 2N5551 are recommended.

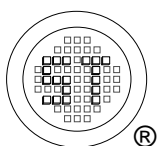
On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	130 160	V
Collector Emitter Voltage	$-V_{CEO}$	120 150	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	600	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$



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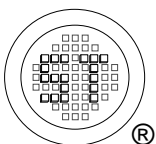


ISO/TS 16949 : 2009 Certificate No. 16073000
ISO14001 : 2004 Certificate No. 71116
ISO 9001 : 2008 Certificate No. 50719410
BS-OHSAS 18001 : 2007 Certificate No. 71116
IECQ QC 080000 Certificate No. PRC-16294-1631

2N5400 / 2N5401

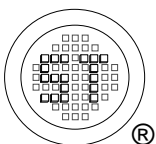
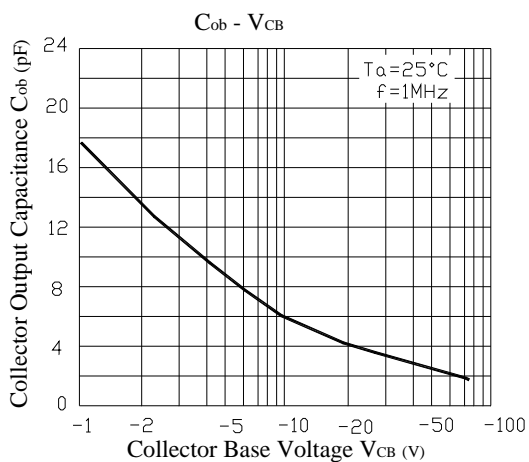
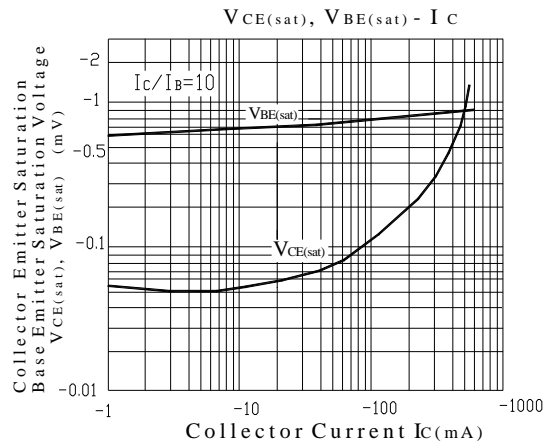
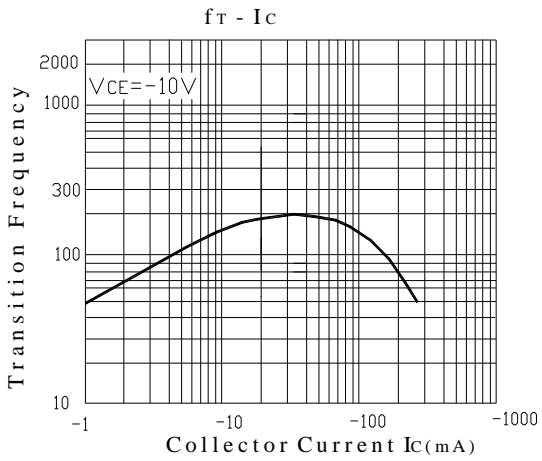
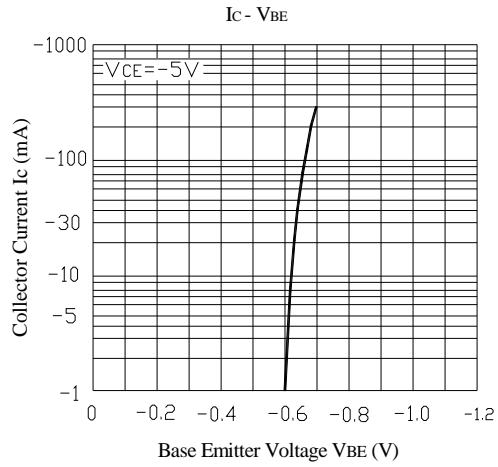
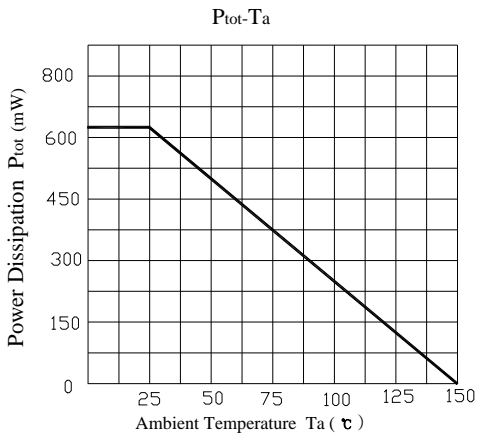
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$	2N5400	h_{FE}	30	-	-
	2N5401	h_{FE}	50	-	-
	2N5400	h_{FE}	40	180	-
	2N5401	h_{FE}	60	240	-
	2N5400	h_{FE}	40	-	-
	2N5401	h_{FE}	50	-	-
Collector Base Cutoff Current at $-V_{CB} = 100\text{ V}$ at $-V_{CB} = 120\text{ V}$	2N5400	$-I_{CBO}$	-	100	nA
	2N5401		-	50	
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$		$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	2N5400	$-V_{(BR)CBO}$	130	-	V
	2N5401		160	-	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	2N5400	$-V_{(BR)CEO}$	120	-	V
	2N5401		150	-	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$		$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$		$-V_{CE(sat)}$	-	0.2	V
			-	0.5	
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$		$-V_{BE(sat)}$	-	1	V
			-	1	
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$		f_T	100	400	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$		C_{ob}	-	6	pF



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